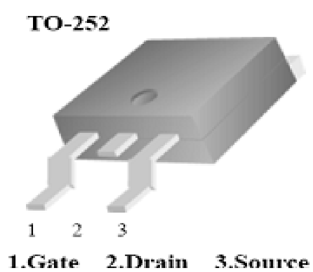
Silicon N-Channel Power MOSFET

CS13J65 A4-G

V_{DSS}	650	V
I_D	13	A
$P_D(T_C$=25℃)	105	W
$R_{DS(ON)max}$	0.42	Ω



General Description:

CS13J65 A4-G, the silicon N-channel Enhanced MOSFETs, is obtained by the super junction technology which reduces the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package type is TO-252, which accords with the RoHS standard.

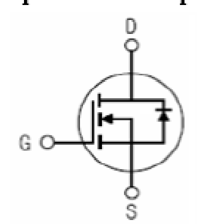
Features:

- **Fast Switching**
- **Low Gate Charge**
- **Low Reverse transfer capacitances**
- **100% Single Pulse avalanche energy Test**
- **Halogen Free**

Applications:

Power switch circuit of adaptor and charger.

Inner Equivalent Principium Chart



Absolute (Tc= 25℃ unless otherwise specified):

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	650	V
I_D	Continuous Drain Current	13	A
I_{DM} [a1]	Pulsed Drain Current	39	A
V_{GS}	Gate-to-Source Voltage	±30	V
E_{AS} [a2]	Single Pulse Avalanche Energy	65	mJ
dv/dt [a3]	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	105	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	–55…+150	℃
T_L	Maximum Temperature for Soldering	300	℃

Electrical Characteristics（Tc= 25℃ unless otherwise specified）:

OFF Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	650	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Bvdss Temperature Coefficient	ID=250uA,Reference25℃	--	0.67	--	V/℃
I_{DSS}	Drain to Source Leakage Current	V_{DS} = 650V, V_{GS}= 0V, T_a = 25℃	--	--	1	μA
		V_{DS} =520V, V_{GS}= 0V, T_a = 125℃	--	--	100	
$I_{GSS(F)}$	Gate to Source Forward Leakage	V_{GS} =+30V	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	V_{GS} =-30V	--	--	-100	nA

ON Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	V_{GS}=10V,I_D=5.5A	--	0.36	0.42	Ω
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.5		4	V
Pulse width tp≤300μs, δ ≤2%						

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D =11A	--	10	--	S
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 50V f = 1.0MHz	--	800	--	pF
C_{oss}	Output Capacitance		--	110	--	
C_{rss}	Reverse Transfer Capacitance		--	7	--	

Resistive Switching Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	I_D = 11 A V_{DD} = 300V R_G =25Ω	--	24	52	ns
tr	Rise Time		--	54	110	
$t_{d(OFF)}$	Turn-Off Delay Time		--	88	180	
t_f	Fall Time		--	25	54	
Q_g	Total Gate Charge	I_D =11A V_{DD} =520V V_{GS} = 10V	--	20	--	nC
Q_{gs}	Gate to Source Charge		--	5	--	
Q_{gd}	Gate to Drain (“Miller”)Charge		--	7	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--		13	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--		26	A
V_{SD}	Diode Forward Voltage	I_S=11A,V_{GS}=0V	--	0.9	1.2	V
trr	Reverse Recovery Time	I_F=I_S T_j = 25℃ dI_F/dt=100A/us, V_{GS}=0V	--	400		ns
Qrr	Reverse Recovery Charge		--	2.4		uC
I_{RRM}	Reverse Recovery Current			12		A

Symbol	Parameter	Max.	Units
$R_{\theta JC}$	Junction-to-Case	1.2	℃/W
$R_{\theta JA}$	Junction-to-Ambient	100	℃/W

[a1]： Repetitive rating; pulse width limited by maximum junction temperature
[a2]： L=10.0mH, Rg=25 Ω， Vdd=50V, Start T_J=25℃
[a3]： I_{SD} =11A,di/dt ≤100A/us,V_{DD}≤BV_{DS}, Start T_J=25℃

Characteristics Curve:

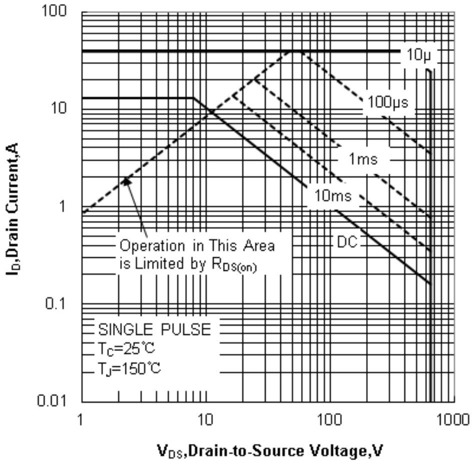


Figure.1 Maximum Forward Bias Safe Operating Area

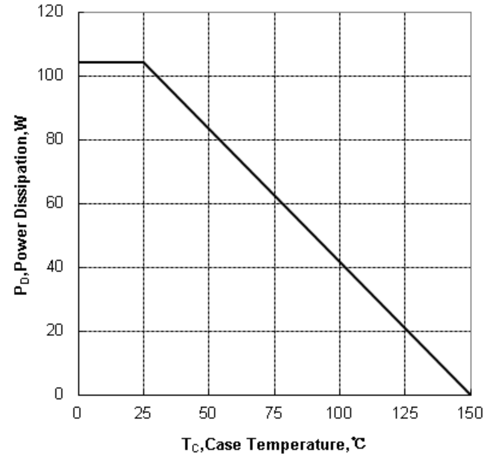


Figure.2 Maximum Power Dissipation vs Case Temperature

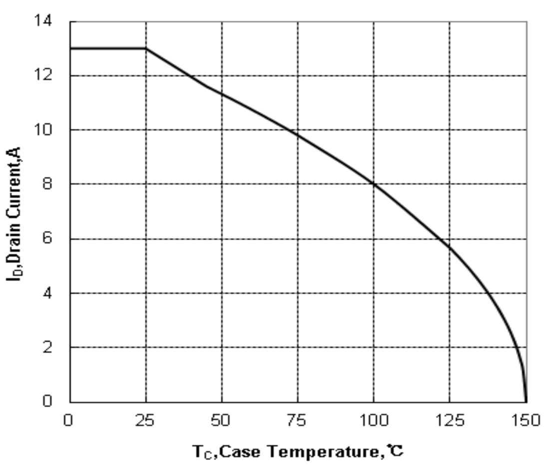


Figure.3 Maximum Continuous Drain Current vs Case Temperature

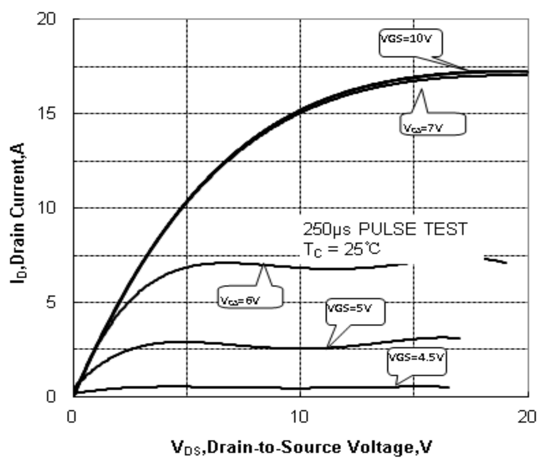


Figure.4 Typical Output Characteristics

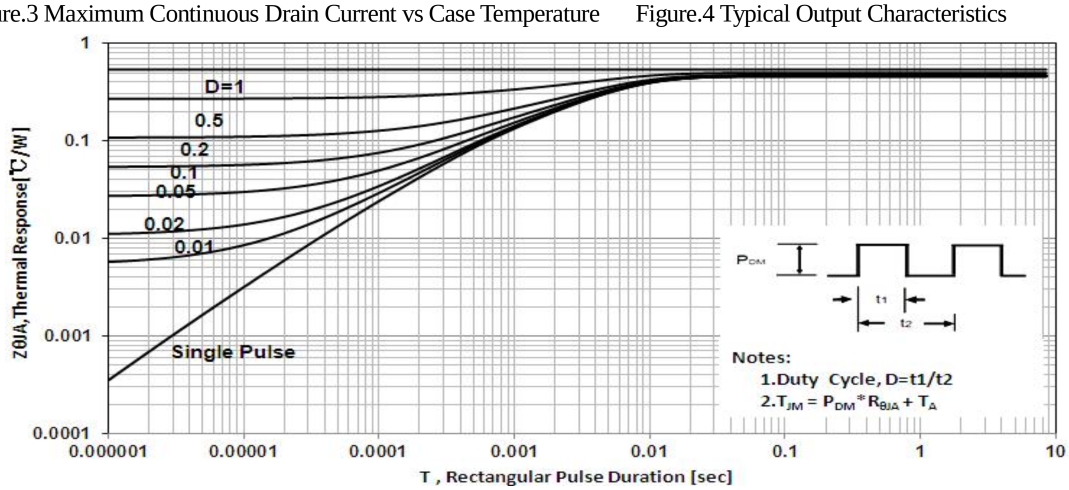


Figure.5 Maximum Effective Thermal Impedance , Junction to Case

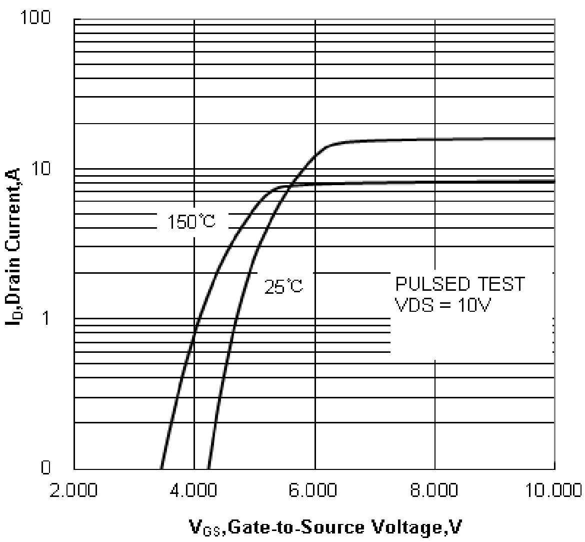


Figure.6 Typical Transfer Characteristics

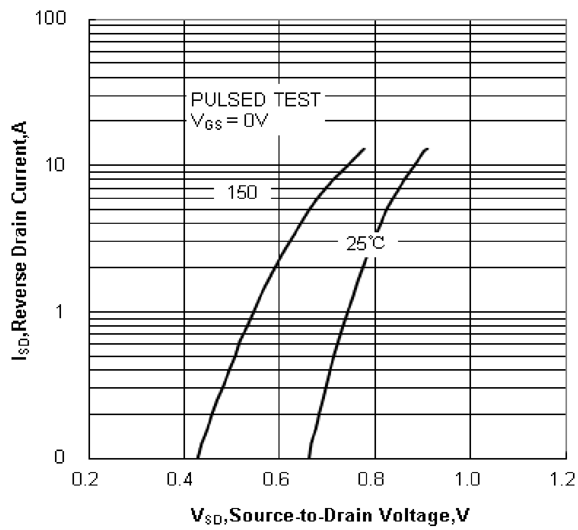


Figure.7 Typical Body Diode Transfer Characteristics

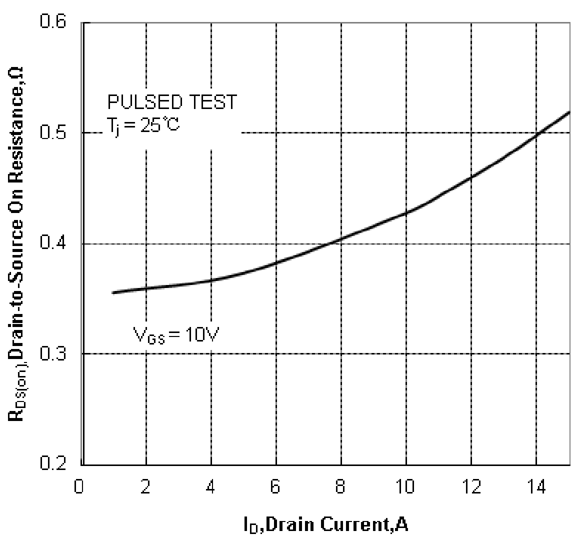


Figure.8 Typical Drain to Source ON Resistance vs Drain Current

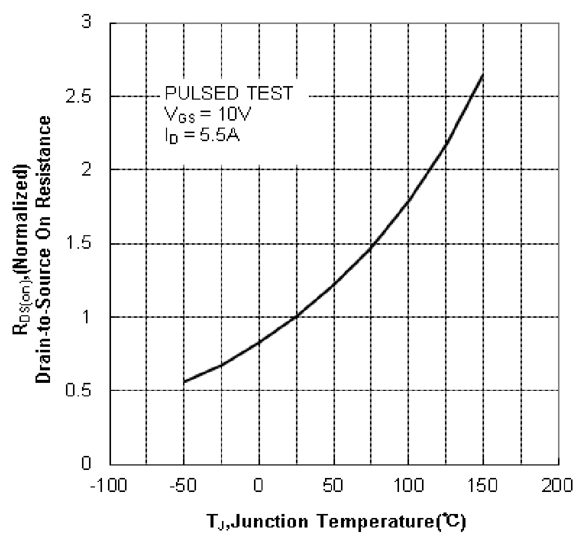


Figure.9 Typical Drian to Source on Resistance vs Junction Temperature

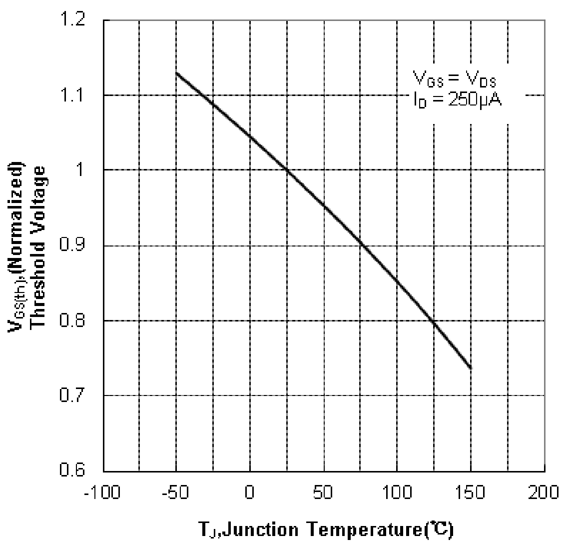


Figure.10 Typical Theshold Voltage vs Junction Temperatur

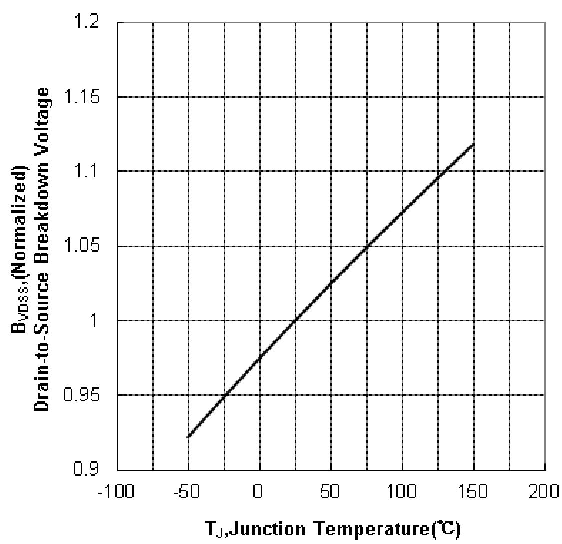


Figure 11 Typical Breakdown Voltage vs Junction Temperature

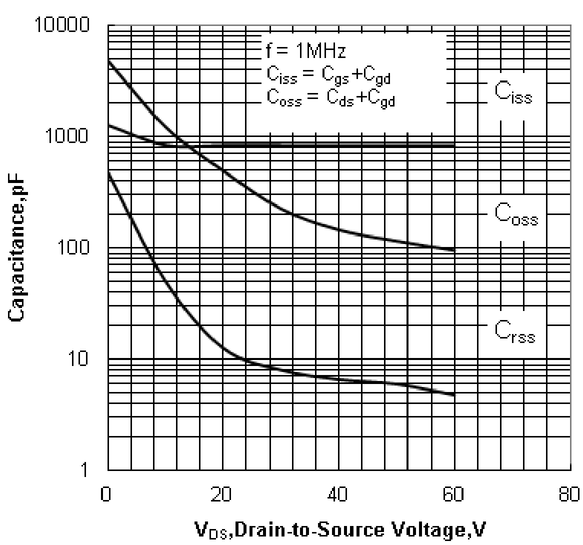


Figure.12 Typical Capacitance vs Drain to Source Voltage

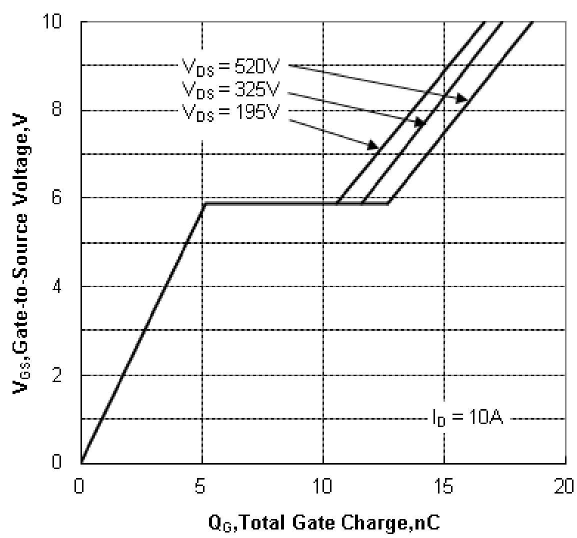


Figure.13 Typical Gate Charge vs Gate to Source Voltage

Test Circuit and Waveform

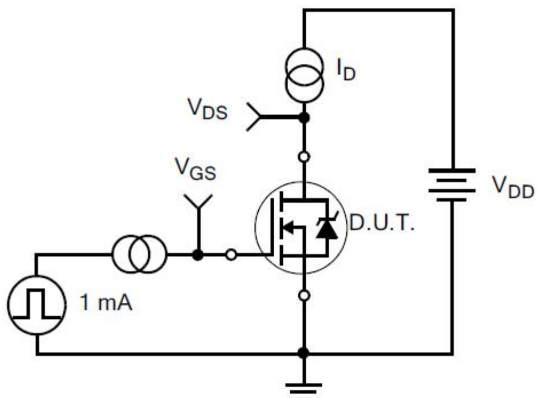


Figure 17. Gate Charge Test Circuit

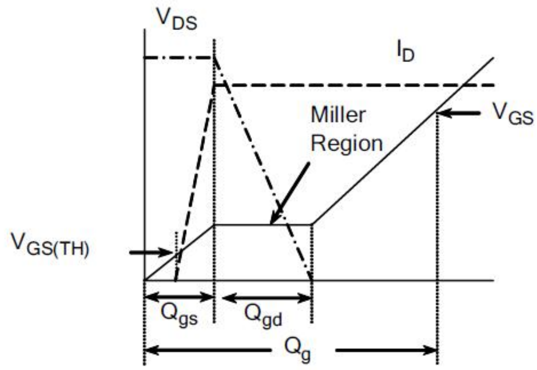


Figure 18. Gate Charge Waveform

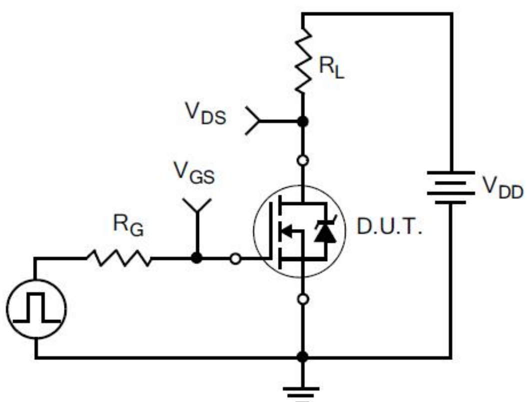


Figure 19. Resistive Switching Test Circuit

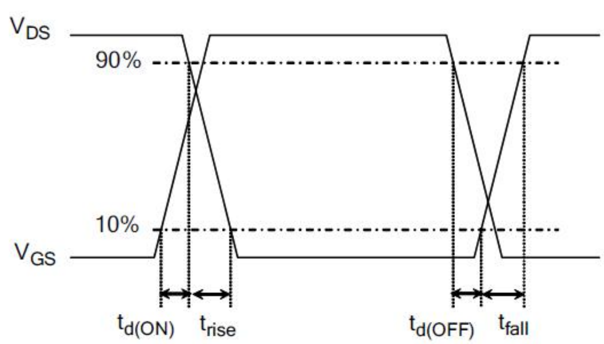


Figure 20. Resistive Switching Waveforms

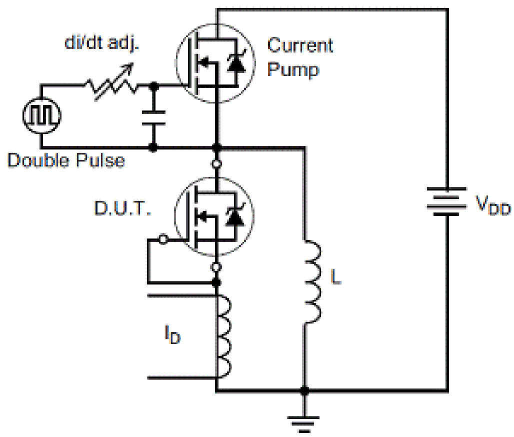


Figure 21. Diode Reverse Recovery Test Circuit

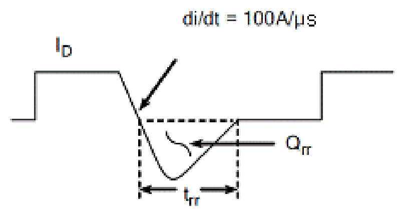


Figure 22. Diode Reverse Recovery Waveform

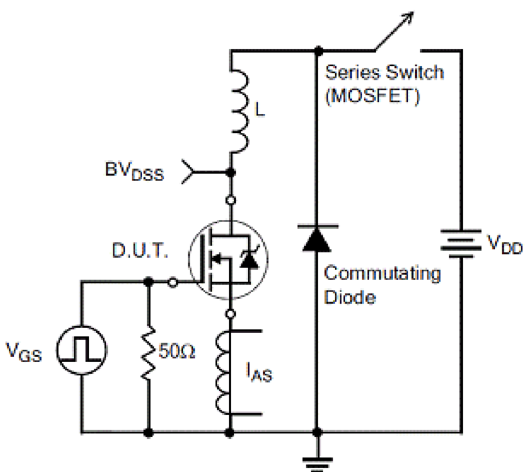
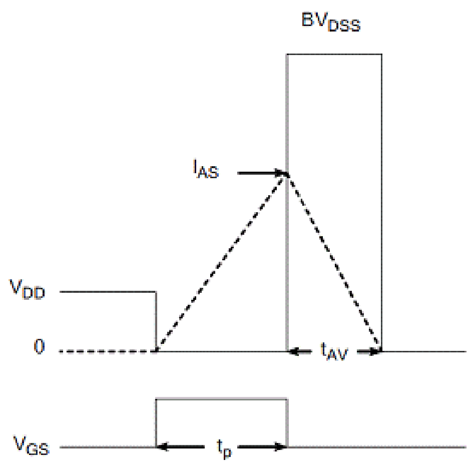


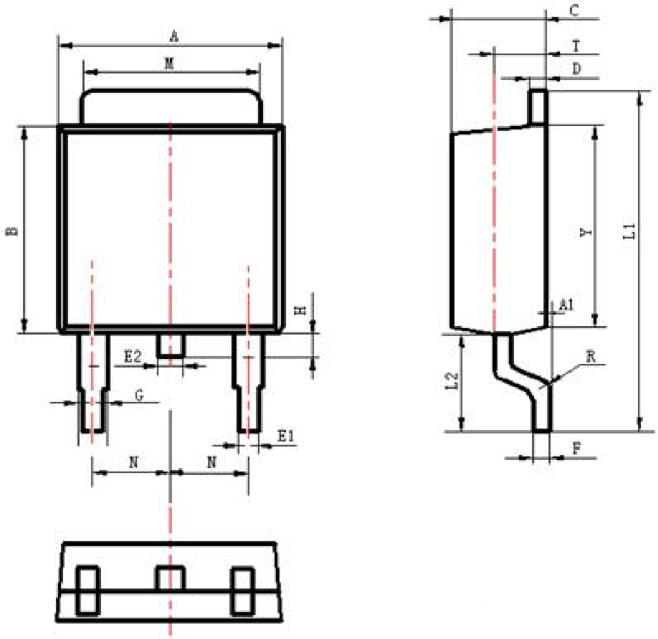
Figure 23. Unclamped Inductive Switching Test Circuit



$$E_{AS} = \frac{I_{AS}^2 L}{2}$$

Figure 24. Unclamped Inductive Switching Waveforms

Package Information



Items	Values(mm)	
	MIN	MAX
A	6.30	6.90
A1	0	0.13
B	5.70	6.30
C	2.10	2.50
D	0.30	0.60
E1	0.60	0.90
E2	0.70	1.00
F	0.30	0.60
G	0.70	1.20
L1	9.60	10.50
L2	2.70	3.10
H	0.60	1.00
M	5.10	5.50
N	2.09	2.49
R	0.3	
T	1.40	1.60
Y	5.10	6.30

TO-252 Package

The name and content of poisonous and harmful material in products

Part's Name	Hazardous Substance									
	Pb	Hg	Cd	Cr(VI)	PBB	PBDE	DIBP	DEHP	DBP	BBP
Limit	≤0.1%	≤0.1%	≤ 0.01%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%	≤0.1%
Lead Frame	○	○	○	○	○	○	○	○	○	○
Molding	○	○	○	○	○	○	○	○	○	○
Chip	○	○	○	○	○	○	○	○	○	○
Wire Bonding	○	○	○	○	○	○	○	○	○	○
Solder	×	○	○	○	○	○	○	○	○	○
Note	○：Means the hazardous material is under the criterion of 2011/65/EU. ×：Means the hazardous material exceeds the criterion of 2011/65/EU. The plumbum element of solder exist in products presently, but within the allowed range of Eurogroup's RoHS.									

Warnings

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. It is suggested to be used under 80 percent of the maximum ratings of the device.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heatsink.
3. VDMOSFET is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. This publication is made by Huajing Microelectronics and subject to regular change without notice.

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